

Laboratory 3: MOSFET characteristics, Current Mirrors, Small Signal Amplifiers

Introduction:

Mosfets and their characteristics are the main topic of this lab. We analyze the DC bias component to these devices and find their use cases. These include current mirrors and amplifiers. We also analyze their real characteristics with small signal models, and find what operating conditions and frequencies they work best in. We perform this analysis with simulation and by building the circuits, with the addition of using Hybrid Pi /T models for fets.

Exercise 3.1 IV Curves

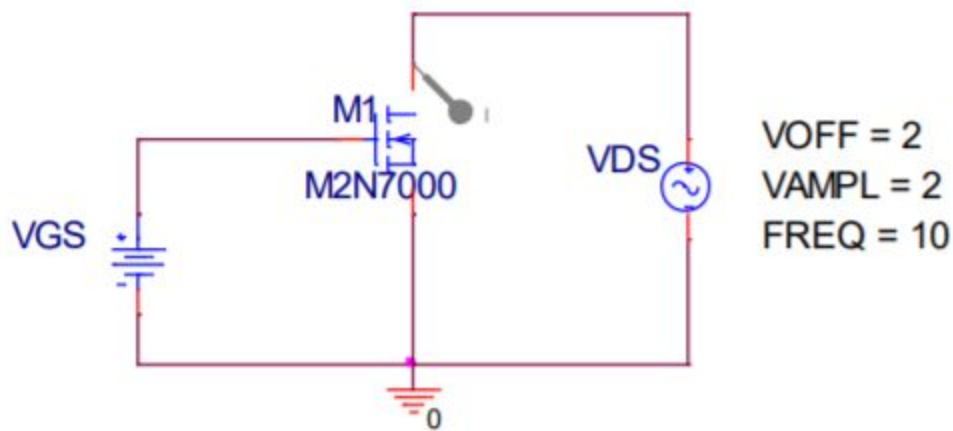


Figure 3.1.1 LTSpice Schematic

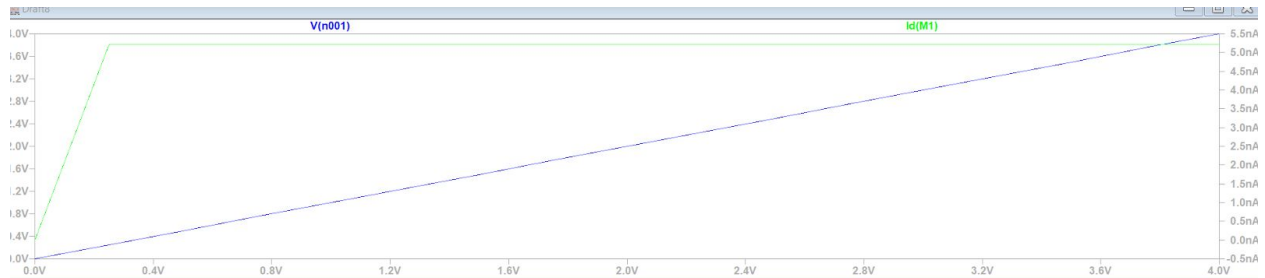


Figure 3.1.2 IV curve from Part 1 $V_{GS} = 1V$

For $V_{GS} = 1V$, the fet is off.



Figure 3.1.3 IV curve $V_{GS} = 2V$

The saturation current is about 13mA.



Figure 3.1.4 IV Curve $V_{GS} = 2.5V$

The saturation current is about 60mA.



Figure 3.1.5 IV Curve $V_{GS} = 3V$

The saturation current is about 140mA.

As V_{GS} increases, the saturation current also increases.

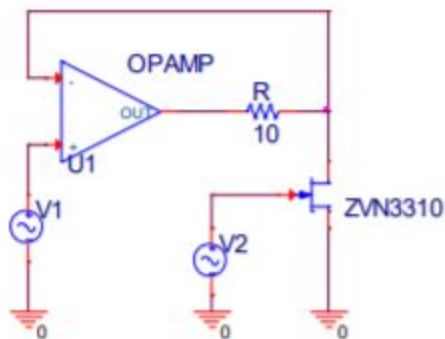


Figure 3.1.6 Circuit Schematic for discovery board

The positive amplifier input, V_1 (V_{DS}), was set to a 0.1V DC using one of the Discovery Board channels and the gate input, V_2 (V_{GS}), was set to the MOSFET to a 1kHz, 3Vpp triangle wave with a 1.5 V DC offset using the other channel.

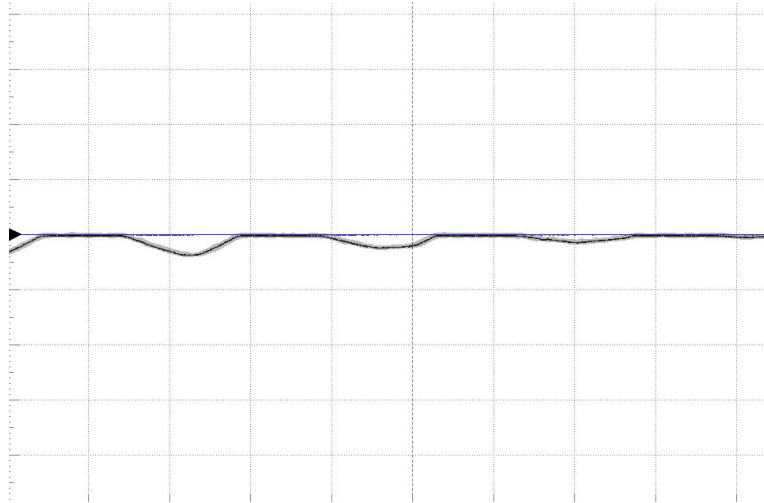


Figure 3.1.7 Current through resistor, I_R

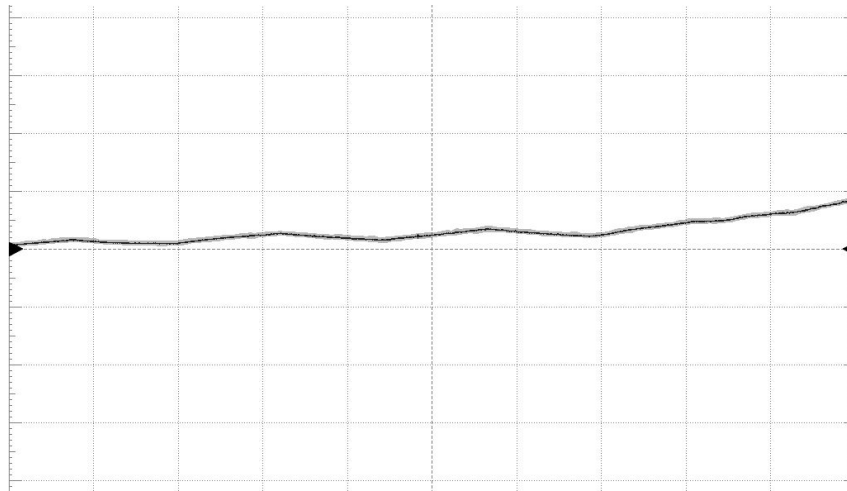


Figure 3.1.8 V_{GS} vs I_D triode

V_{DS} , or V_1 was set to a 1kHz, 5Vpp triangle wave with a 2.5V DC offset using the other channel. V_2 (V_{GS}) was set to DC and the gate input was adjusted such that you could start to see current flowing through the resistor. This threshold was compared to earlier estimations. The gate voltage was increased by 0.04V (DC) such that a larger current through the resistor was visible.

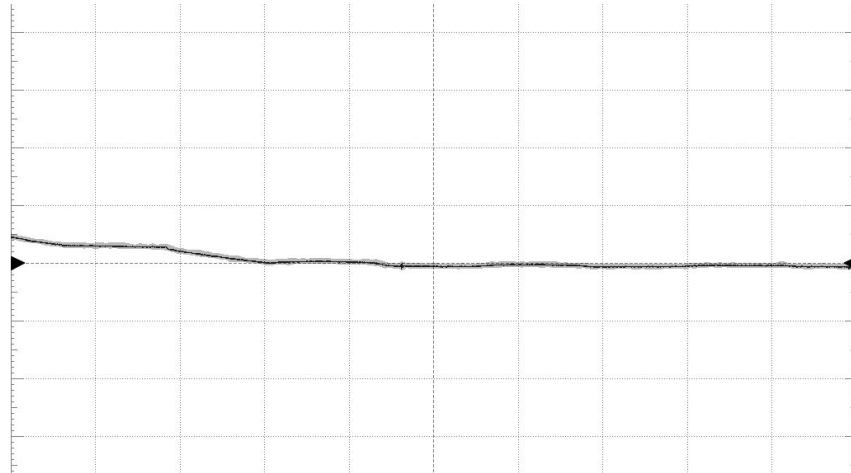


Figure 3.1.9 I_D vs V_{GS} with added .04 v

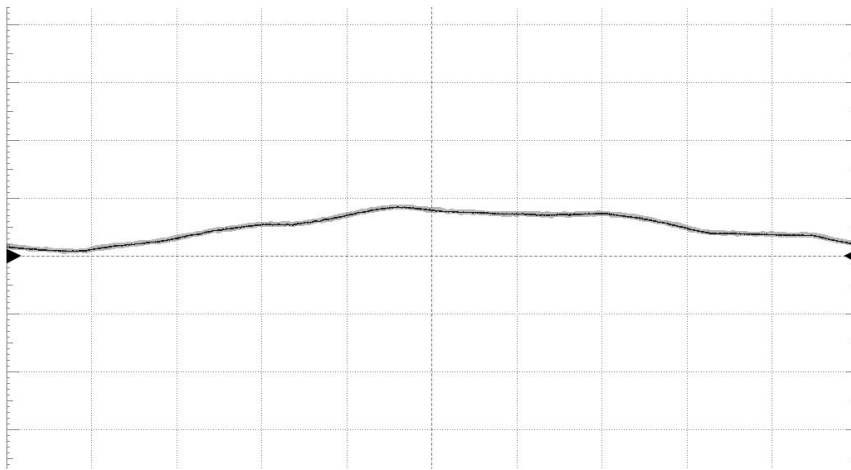


Figure 3.1.10 I_D vs V_{GS} with another added .04 v(.08V total added)

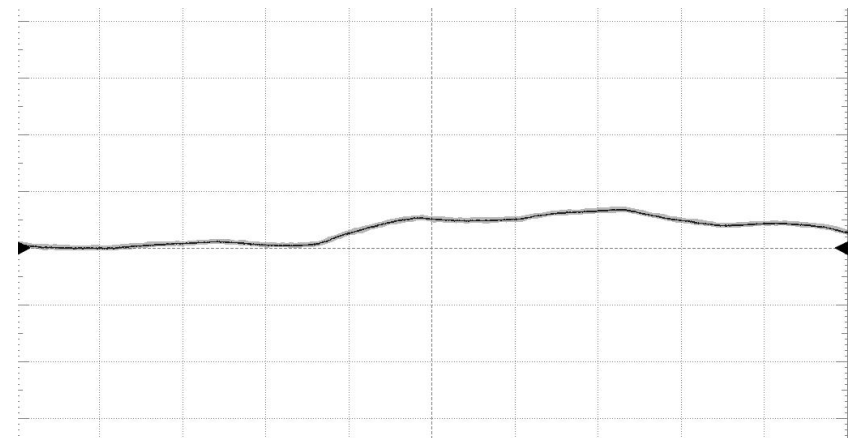


Figure 3.1.10 I_D vs V_{GS} with another added .04 v(.12 V total added)

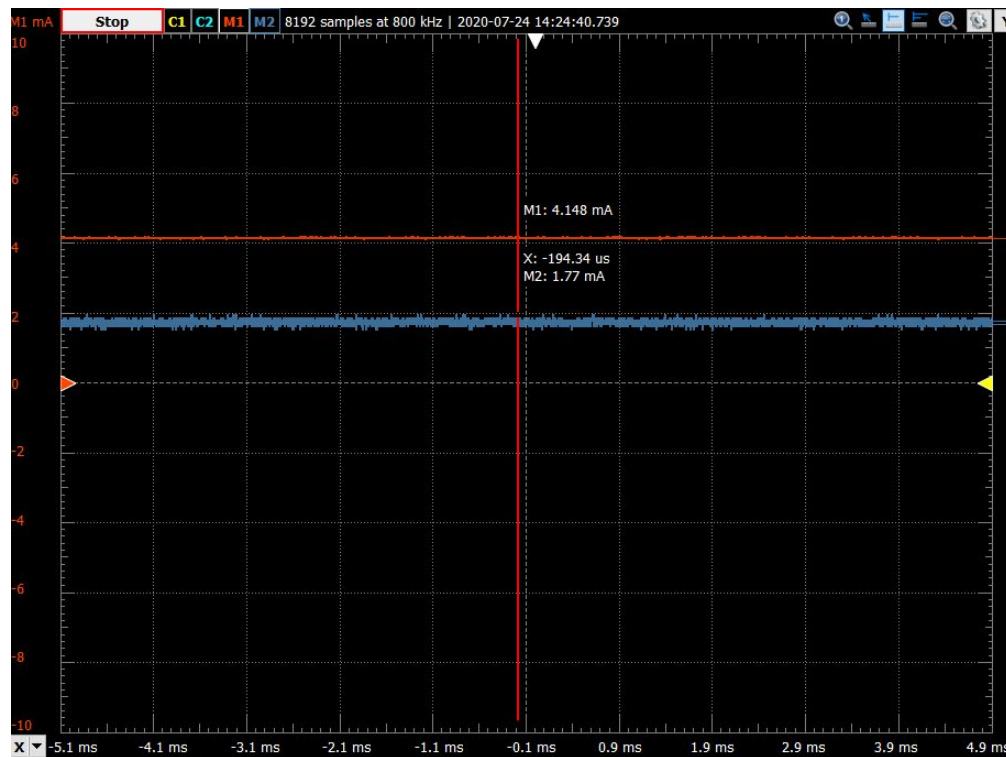
The K_n value was found to be about $.035 \text{ A/V}^2$ and the V_{TN} was about $\sim 2.1\text{V}$.

Exercise 3.2: Current Mirror

We have a current limitation so we start with 47 ohms.

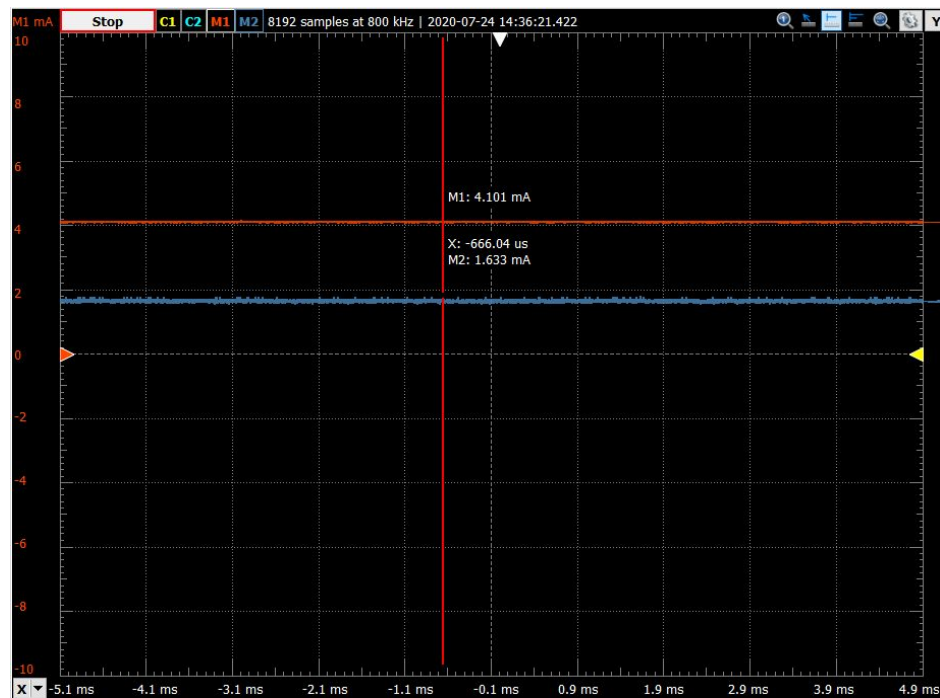
Red is Fet 1 with a constant 470 resistor and Blue is Fet 2 with variable resistors

Current Mirror with $R_2 = 47$ ohms

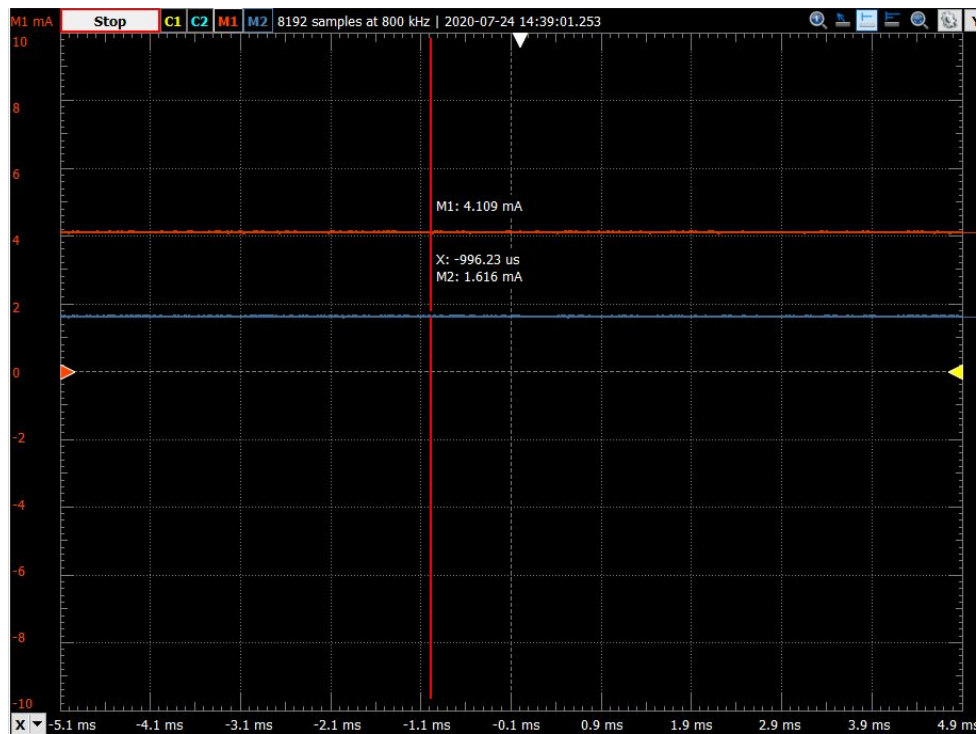


Based on the part 1 results, the current mirror is not exactly working as expected. However there are reasons for this. The math channels that measure the current divide by a constant that may not be the exact value of the resistor. Furthermore the scopes themselves act as some noise for voltage calculation.

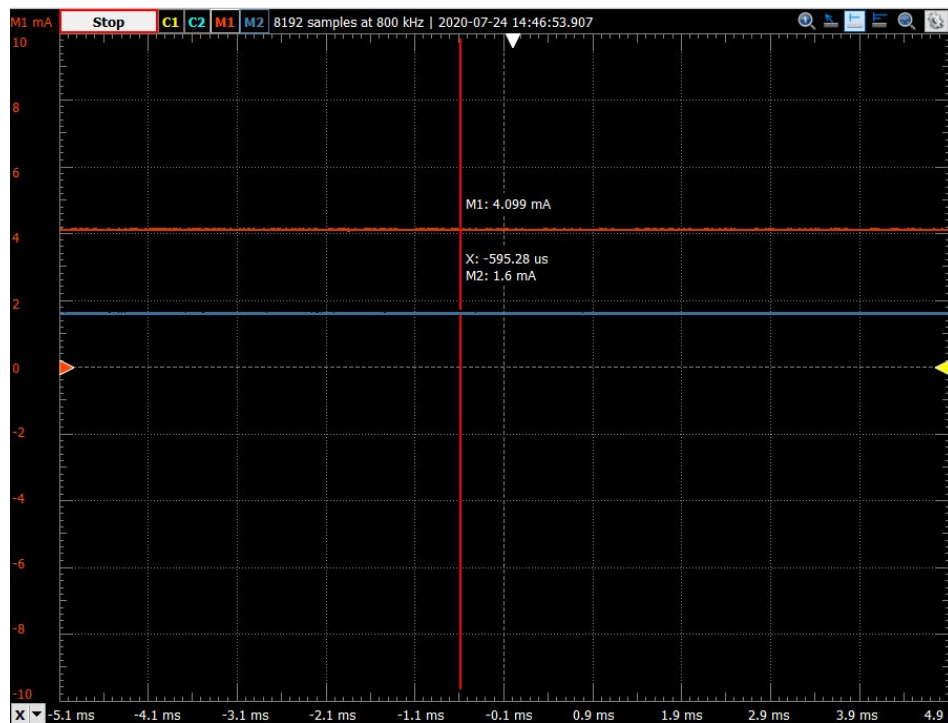
Current Mirror with $R_2 = 100\ \Omega$



Current Mirror with $R_2 = 470\ \Omega$



Current Mirror with $R_2 = 1\text{ k}\Omega$



Current Mirror with $R_2 = 10\text{ k}\Omega$

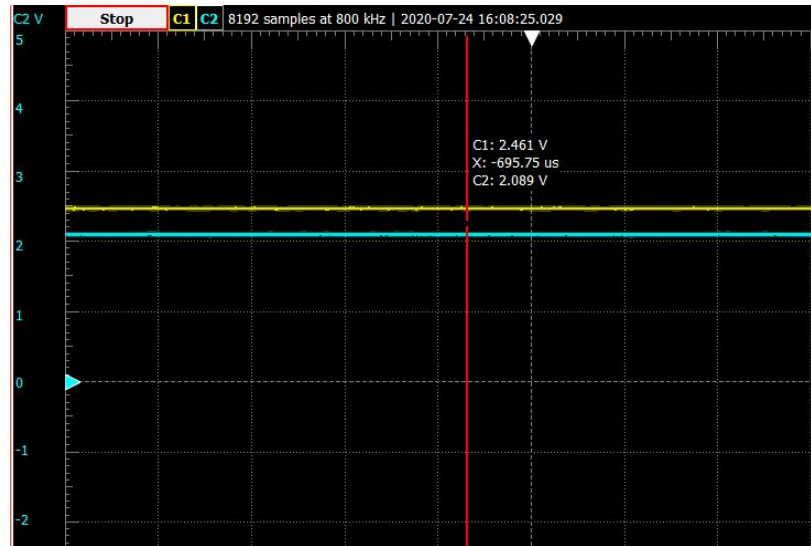


While the current mirror did not show the same current, as measured by the scope, it did manage to keep the distance between the two measurements consistent. From 47 ohms to 1k ohms, the current measured by the scope for both fets were the same. This means that while the components, and our instruments are not exactly identical, they principle of the current mirror is held.

The current mirror fails working over the 1k ohms as we measured. This result is somewhat consistent as the fet is now in deep triode.

Exercise 3.3: DC Biasing

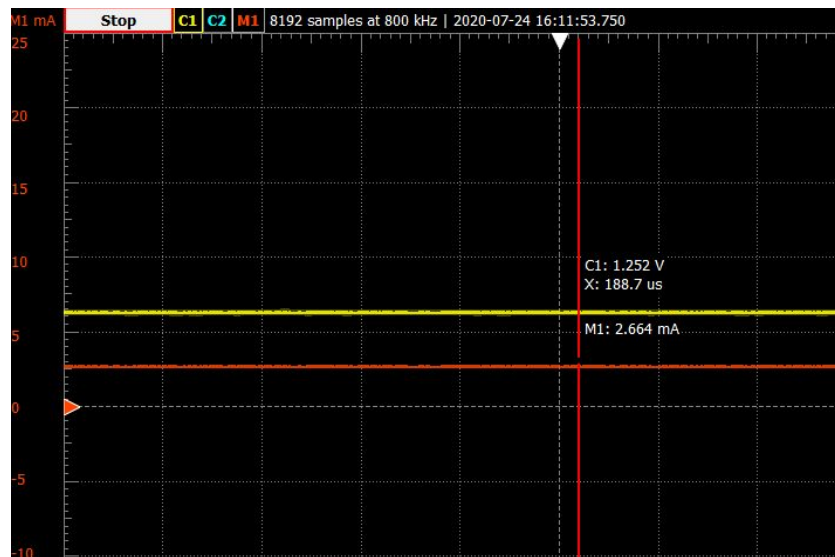
Measurement of VDS and VGS



Yellow = VDS, Blue = VGS

VDS = 2.46V

VGS = 2.09V



Yellow = VRS, Red = $I_{rs} = I_D = 2.67\text{mA}$

The fet is verified to be in saturation. The measured values match roughly to the calculated values.

Exercise 3.4 Common source amplifiers – Amplifier characteristics

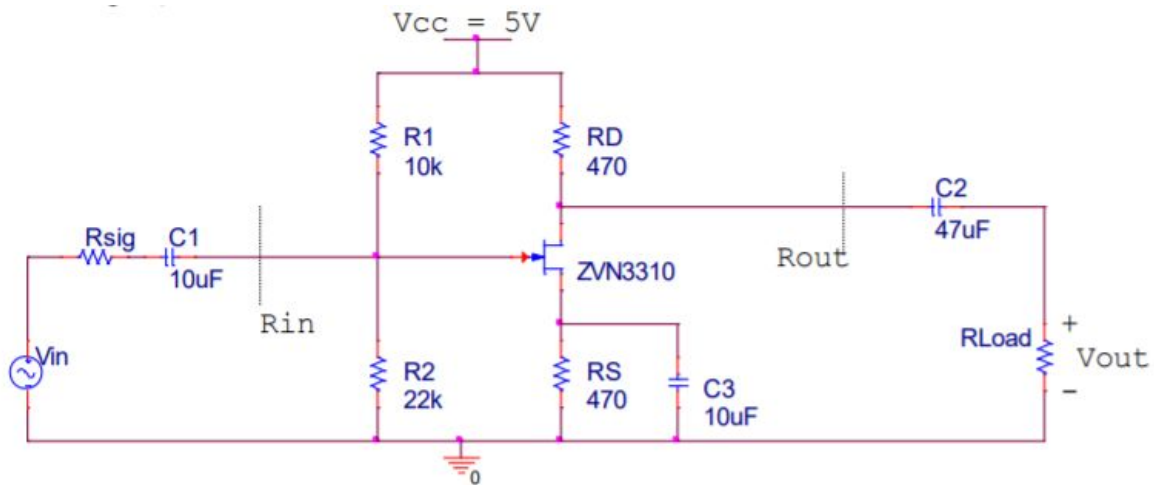
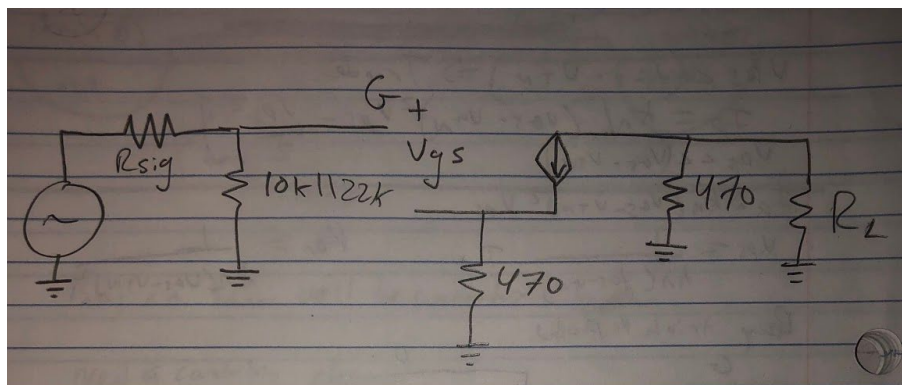


Figure 3.4.1 Circuit to be implemented in part 3.4



Avo was calculated to be 1.35 using $R_{sig} = 0$ and $R_L = \infty$, this is acceptable because in the setup we are using 100 and 100k, which have high enough and low enough magnitudes.

My estimated values for Avo was 1.3

Figure 3.4.2 Small signal Model

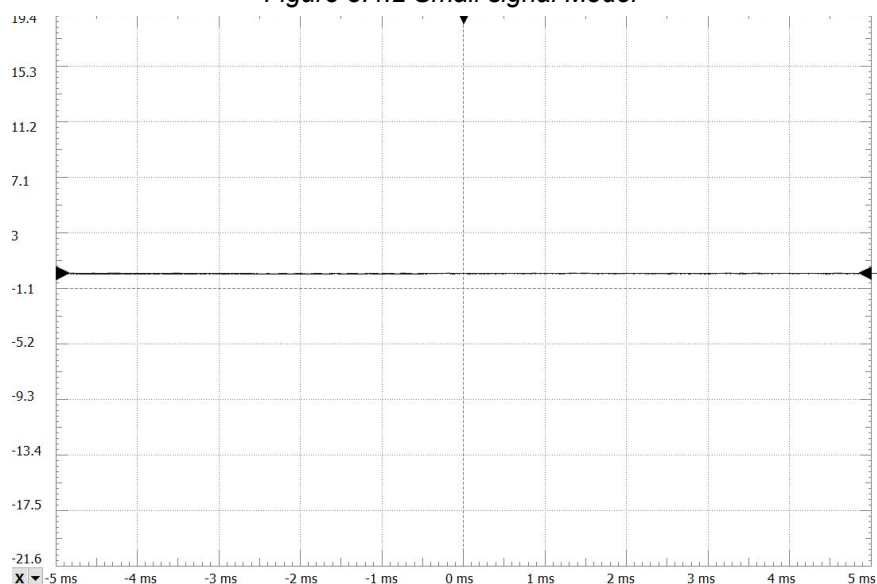


Figure 3.4.3 Output Voltage

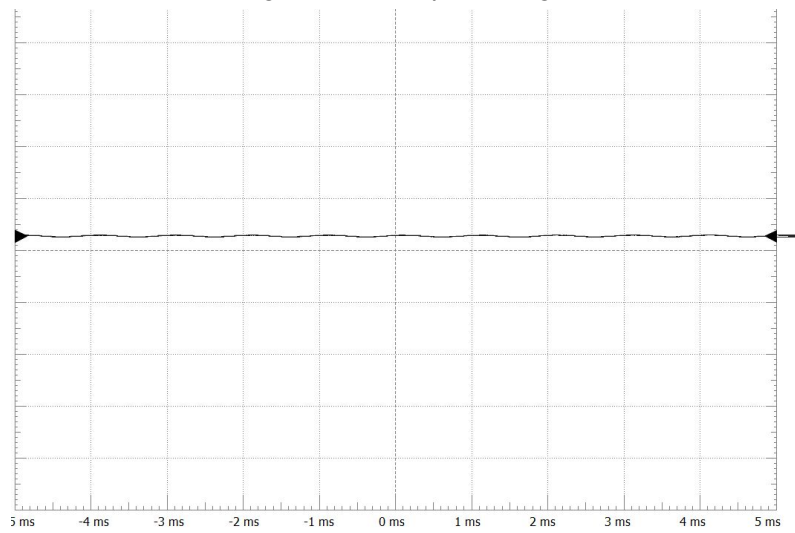


Figure 3.4.4 Current through R_{sig}

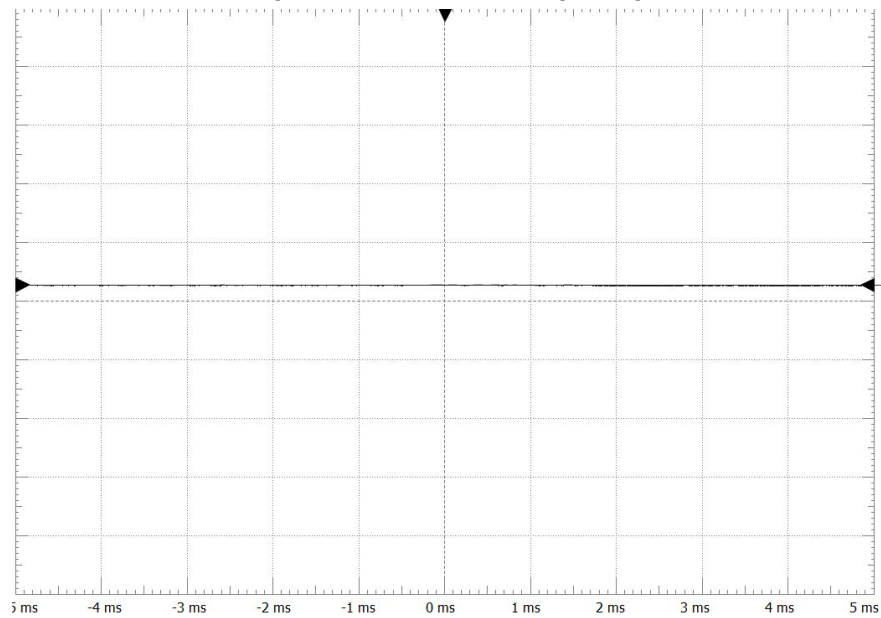


Figure 3.4.5 Current through $R_{sig} = 4.7k$ $R_{load} = 470$

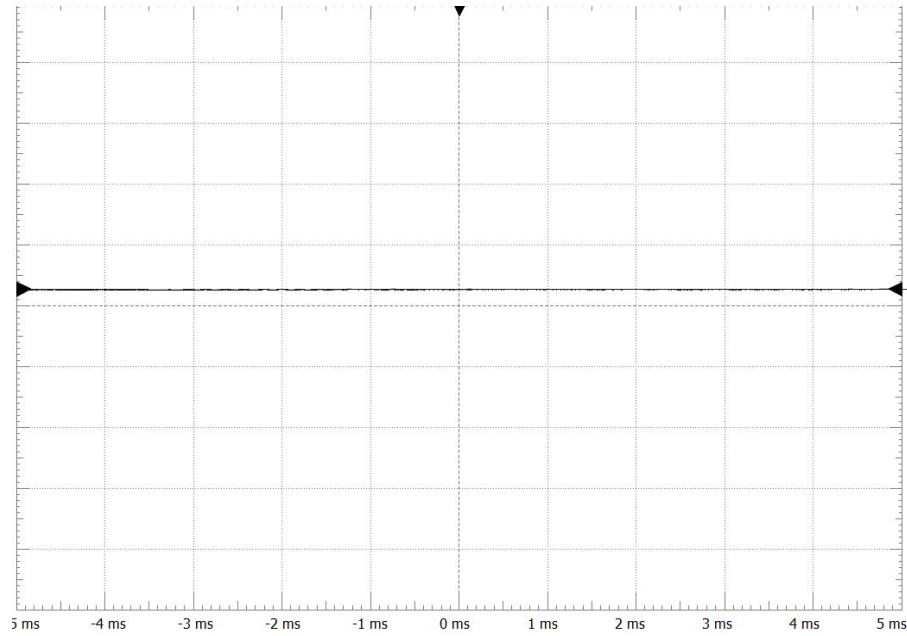


Figure 3.4.6 Current through R_{sig} without capacitor

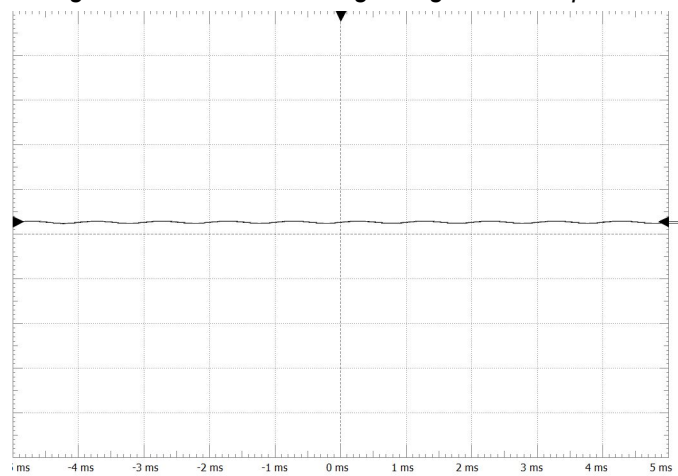


Figure 3.4.7 Current through R_{sig} without capacitor, with $R_{sig} = 4.7k$ $R_{load} = 470$

Without the capacitor, the values increase as the capacitor dampens the output.

Exercise 3.5: Common Source Amplifier - Bandwidth

$$C_{iss} = C_{gd} + C_{gs}$$

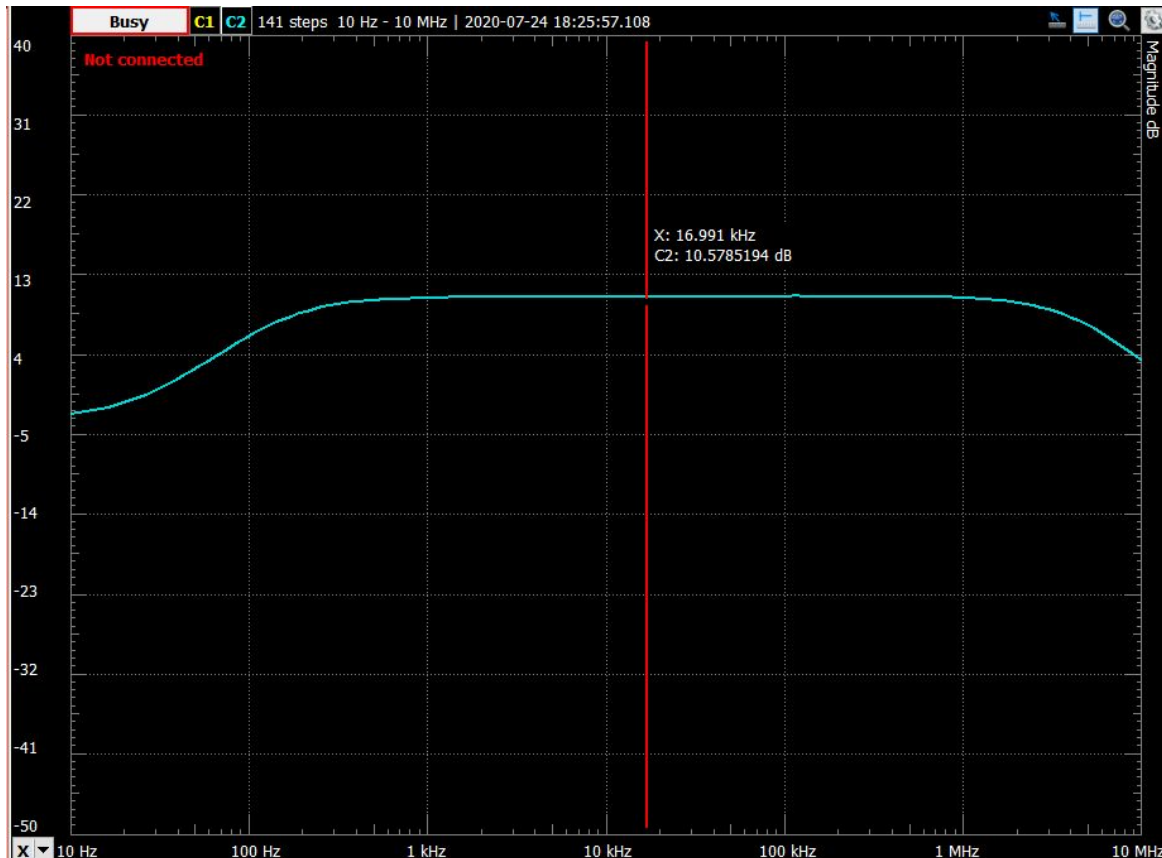
$$C_{oss} = C_{ds} + C_{gd}$$

$$C_{rss} = C_{gd}$$

Thus:

$$C_{GD} = 5 \text{ pF} ; C_{GS} = 35 \text{ pF} ; C_{DS} = 10 \text{ pF}$$

Frequency Sweep



We have a pass band from 200Hz to 1 MHz

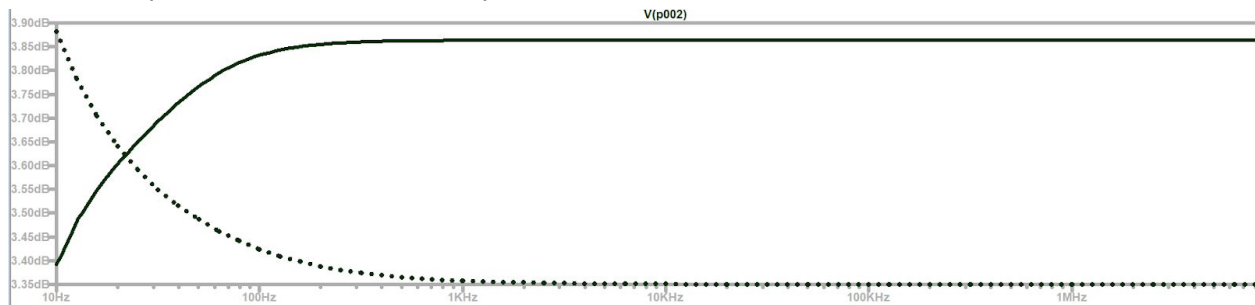
The circuit results match what we have in part 4.

We can see this in Figure 3.4.1 with the capacitors included. The cap responsible for the low band is C1 and the high band cap is CDS.

R_{sig} is part of the input resistance seen by the cap which means it is directly affected by the RC circuit and its rolloff frequency. The same reason as to why changing R_{Load} affects the results. R_{Load} is a resistor seen by the output cap changing the RC circuit.

The 10kHz was a good choice because it operates well within the pass band of the common source amplifier. At this frequency the caps are not affecting the circuit output.

LTSpice of Common Source Amplifier



We can see that the simulated results match decently well with the experimental results. The experimental problem we see is the rolloff at 1 MHz. This is due to internal capacitance that is parasitic. This means that we have a band of frequencies that we have to operate within. What can be done is increasing the band on the low cut off side, but pushing it back. You can choose different resistors and caps to keep the fet in saturation but also decrease the low - high frequency part of the band.

Conclusion:

Fets draw the same interest as diodes, and in a way they are the step up from diodes. They serve as another method for signal control and current flow. Fets are very interesting as we want them to be in saturation for quite a bit of operation. This is because their output is predictable at this point. If it's in deep triode or triode we aren't likely to get the output we want. This is shown with the current mirror exercise. Fets also have the ability to act as amplifiers. Even though you can hook them up differently to get the amplifier you want, nothing will change the parasitic capacitance of a real fet. This causes the fet to act like a bandpass filter. When using fets to design you have to be cognisant of these traits.